

DATA SHEET



NPN SILICON RF TRANSISTOR NE664M04 / 2SC5754 JEITA Part No.

NPN SILICON RF TRANSISTOR FOR MEDIUM OUTPUT POWER AMPLIFICATION (0.4 W) FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04)

FEATURES

- Ideal for 460 MHz to 2.4 GHz medium output power amplification
- P_O (1 dB) = 26.0 dBm TYP. @ $V_{CE} = 3.6$ V, $f = 1.8$ GHz, $P_{in} = 15$ dBm
- High collector efficiency: $\eta_C = 60\%$
- UHSO-HV technology ($f_T = 25$ GHz) adopted
- High reliability through use of gold electrodes
- Flat-lead 4-pin thin-type super minimold (M04) package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE664M04-A 2SC5754-A	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 1 (Emitter), Pin 2 (Collector) face the perforation side of the tape
NE664M04-T2-A 2SC5754-T2-A	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^{\circ}\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	13	V
Collector to Emitter Voltage	V_{CEO}	5.0	V
Emitter to Base Voltage	V_{EBO}	1.5	V
Collector Current	I_C	500	mA
Total Power Dissipation	P_{tot}^{Note}	735	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^{\circ}\text{C}$

Note Mounted on 38×38 mm, $t = 0.4$ mm polyimide PCB

THERMAL RESISTANCE

Parameter	Symbol	Test Conditions	Ratings	Unit
★ Junction to Ambient Resistance	$R_{th\ j-a1}$	Mounted on 38×38 mm, $t = 0.4$ mm polyimide PCB	170	$^{\circ}\text{C/W}$
	$R_{th\ j-a2}$	Stand alone device in free air	570	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	1 000	nA
Emitter Cut-off Current	I _{EBO}	V _{BE} = 1 V, I _C = 0 mA	–	–	1 000	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 3 V, I _C = 100 mA	40	60	100	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 100 mA, f = 0.5 GHz	16	20	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 3 V, I _C = 100 mA, f = 2 GHz	5.0	6.5	–	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 3 V, I _E = 0 mA, f = 1 MHz	–	1.0	1.5	pF
Maximum Available Power Gain	MAG ^{Note 3}	V _{CE} = 3 V, I _C = 100 mA, f = 2 GHz	–	12.0	–	dB
Linear Gain	G _L	V _{CE} = 3.6 V, I _{CQ} = 20 mA, f = 1.8 GHz, P _{in} = 0 dBm, 1/2 Duty	–	12.0	–	dB
Gain 1 dB Compression Output Power	P _O (1 dB)	V _{CE} = 3.6 V, I _{CQ} = 4 mA, f = 1.8 GHz, P _{in} = 15 dBm, 1/2 Duty	–	26.0	–	dBm
Collector Efficiency	η _C	V _{CE} = 3.6 V, I _{CQ} = 4 mA, f = 1.8 GHz, P _{in} = 15 dBm, 1/2 Duty	–	60	–	%

Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%

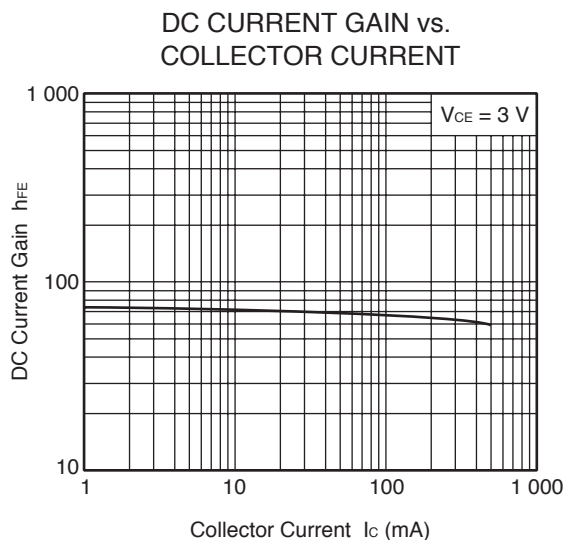
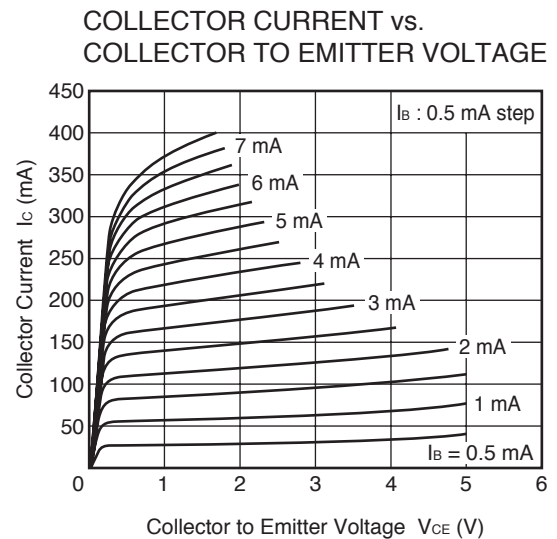
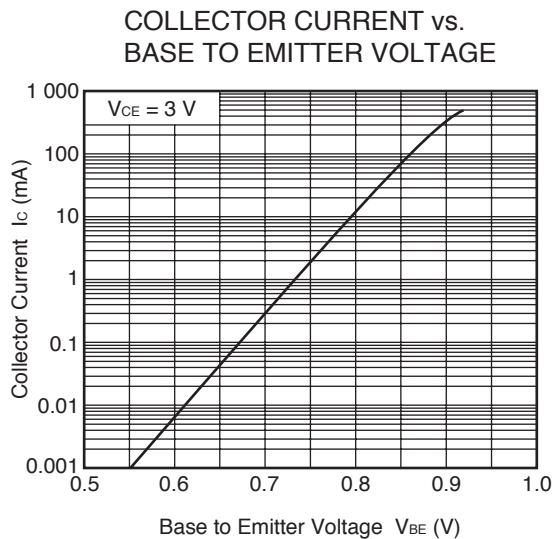
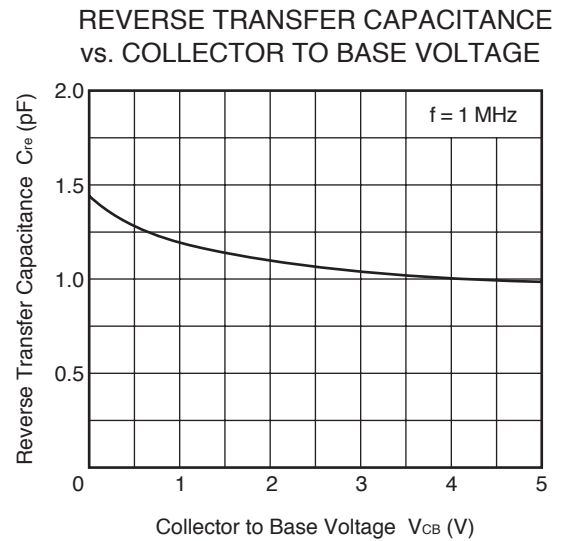
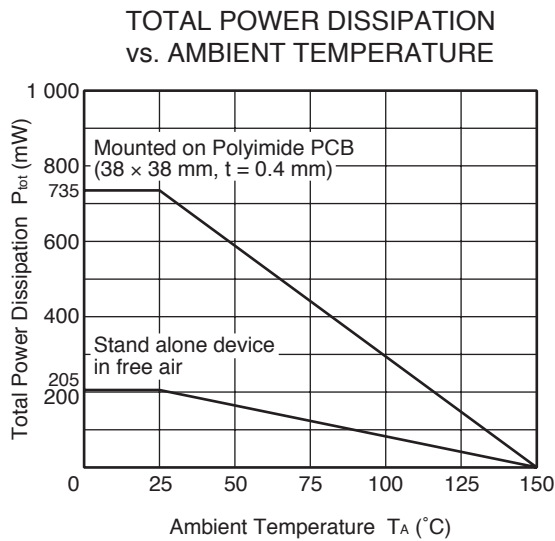
2. Collector to base capacitance when the emitter grounded

$$3. \text{ MAG} = \left| \frac{S_{21}}{S_{12}} \right| (K - \sqrt{K^2 - 1})$$

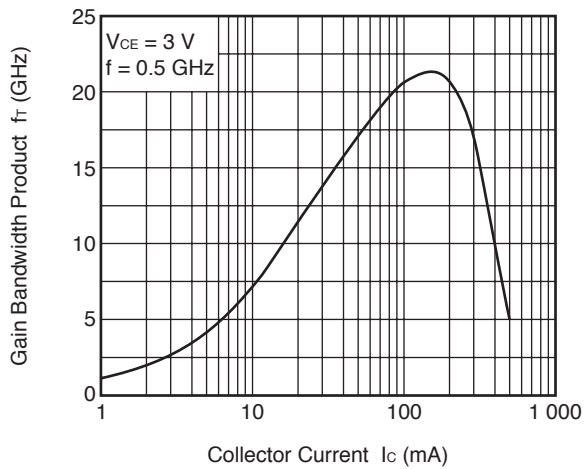
h_{FE} CLASSIFICATION

Rank	FB
Marking	R57
h _{FE} Value	40 to 100

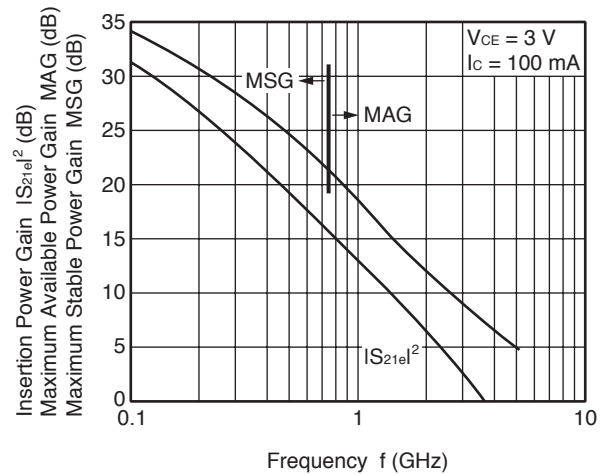
TYPICAL CHARACTERISTICS (Unless otherwise specified, $T_A = +25^\circ\text{C}$)



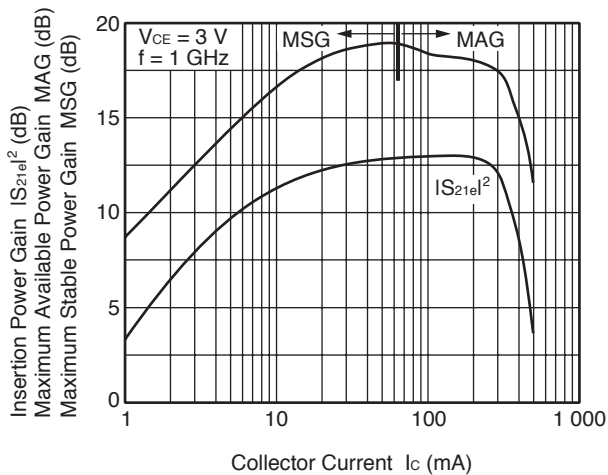
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



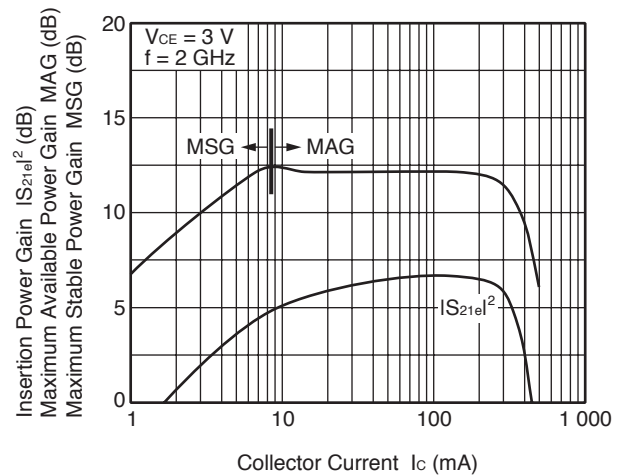
INSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY



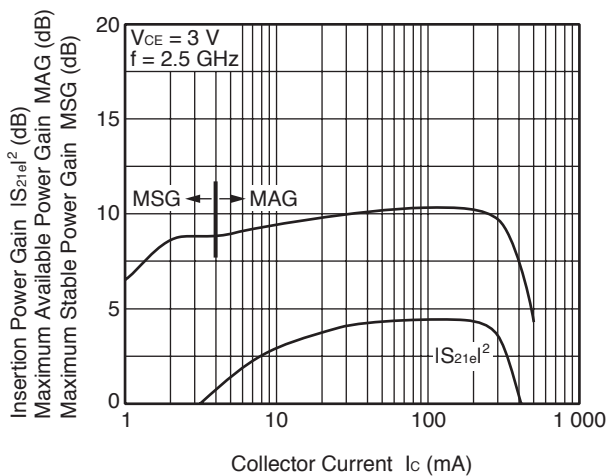
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



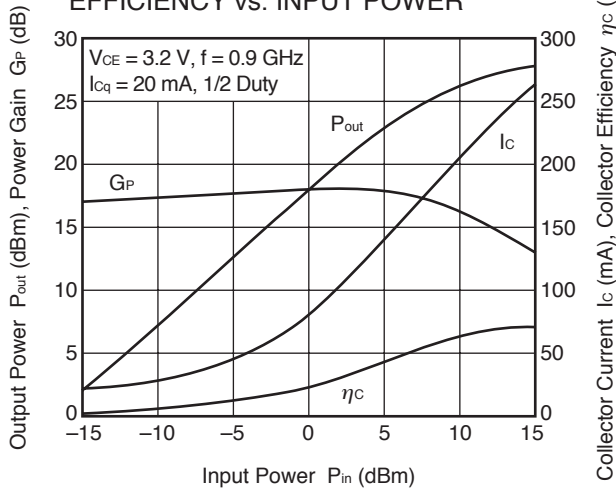
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



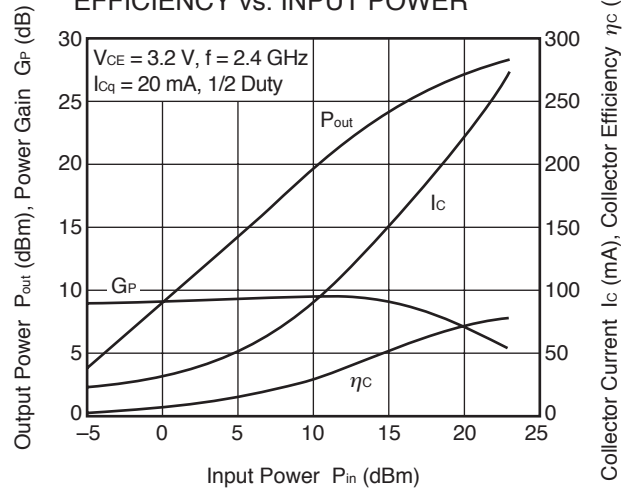
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



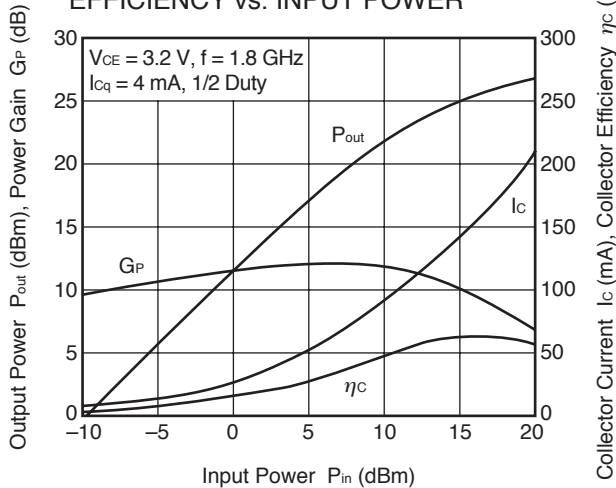
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



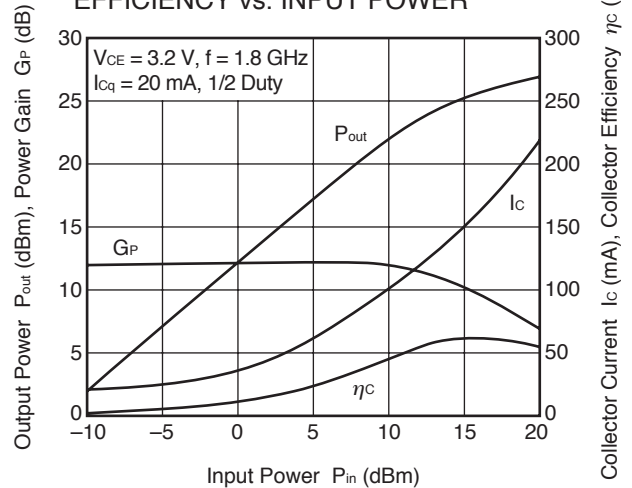
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



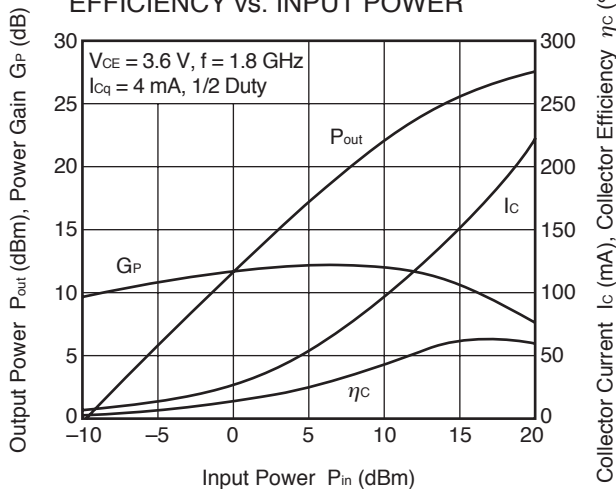
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



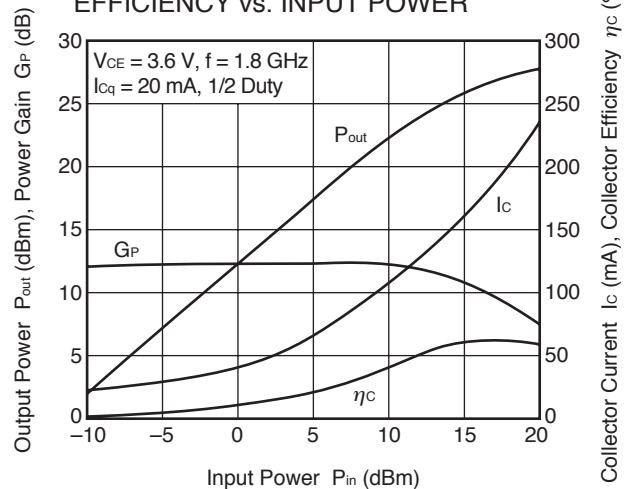
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



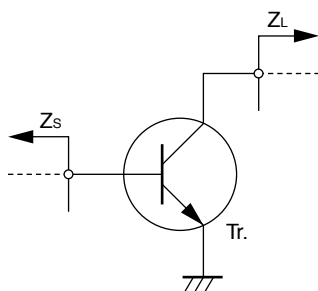
OUTPUT POWER, POWER GAIN,
COLLECTOR CURRENT, COLLECTOR
EFFICIENCY vs. INPUT POWER



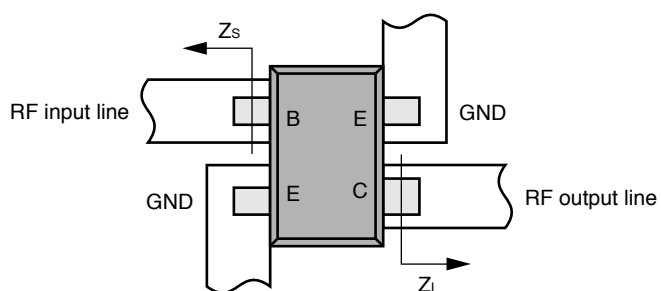
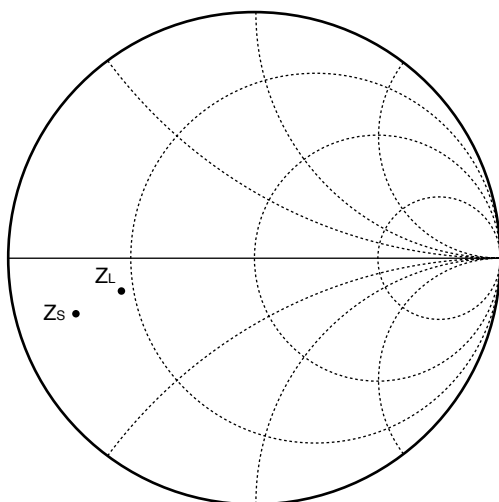
Remark The graphs indicate nominal characteristics.

POWER SUPPLY IMPEDANCE, LOAD IMPEDANCE (Recommended value)

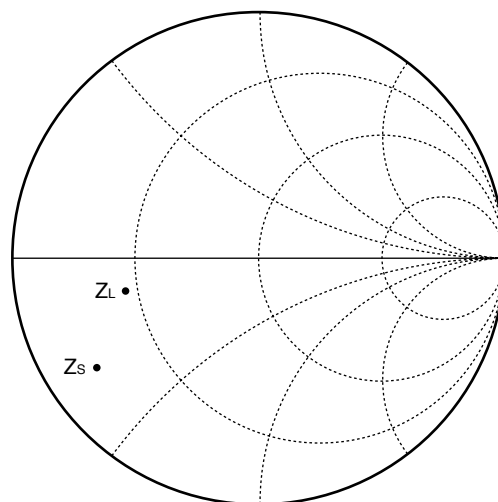
Frequency f (GHz)	Collector to Emitter Voltage V_{CE} (V)	Supply Impedance Z_s (Ω)	Load Impedance Z_L (Ω)
0.9	2.8 to 3.6	8.4 – 5.2 j	15.1 – 4.3 j
1.8	2.8 to 3.6	6.3 – 16.4 j	15.8 – 6.9 j
2.4	2.8 to 3.6	5.9 – 22.1 j	15.2 – 17.9 j



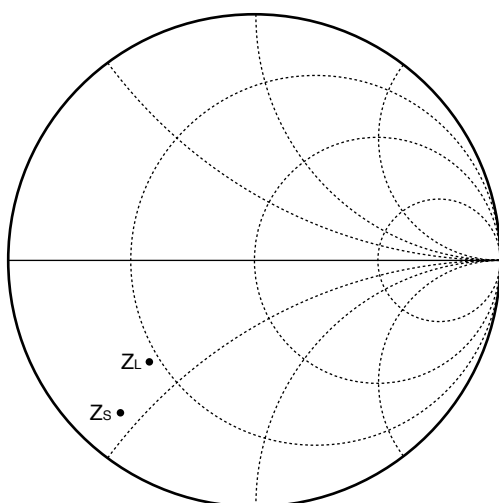
f = 0.9 GHz



f = 1.8 GHz

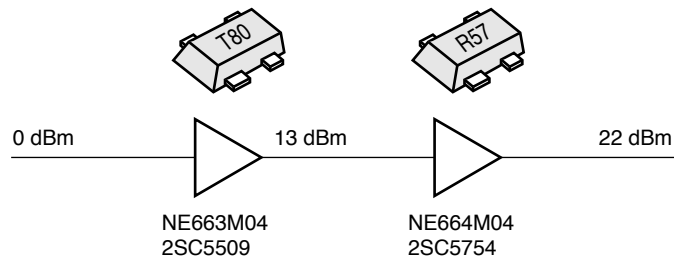


f = 2.4 GHz

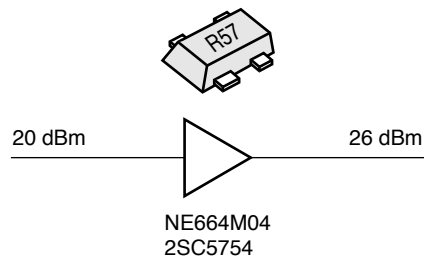


APPLICATION EXAMPLE (Low-cost PA solution)

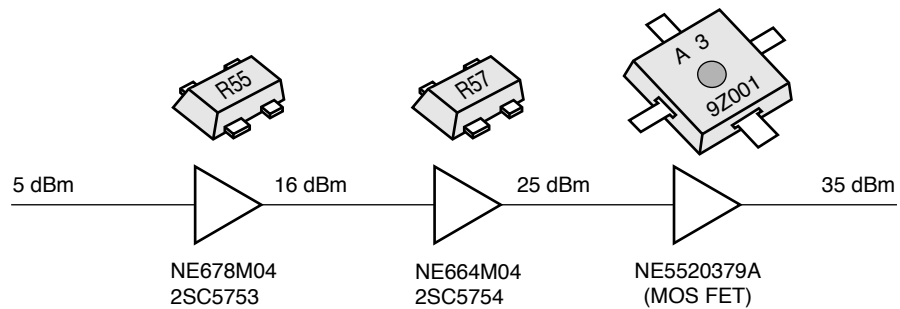
Bluetooth Power Class 1
f = 2.4 GHz



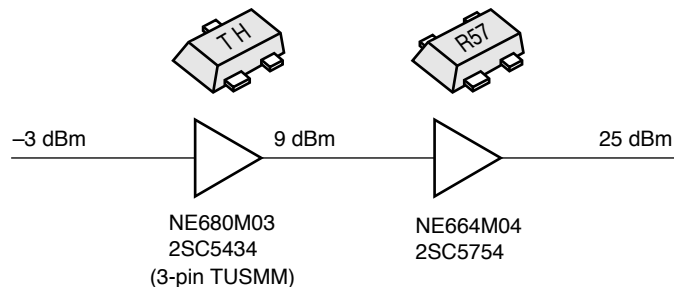
SS Cordless Phone
f = 2.4 GHz



DCS1800 (GSM1800) Cellular Phone
f = 1.8 GHz

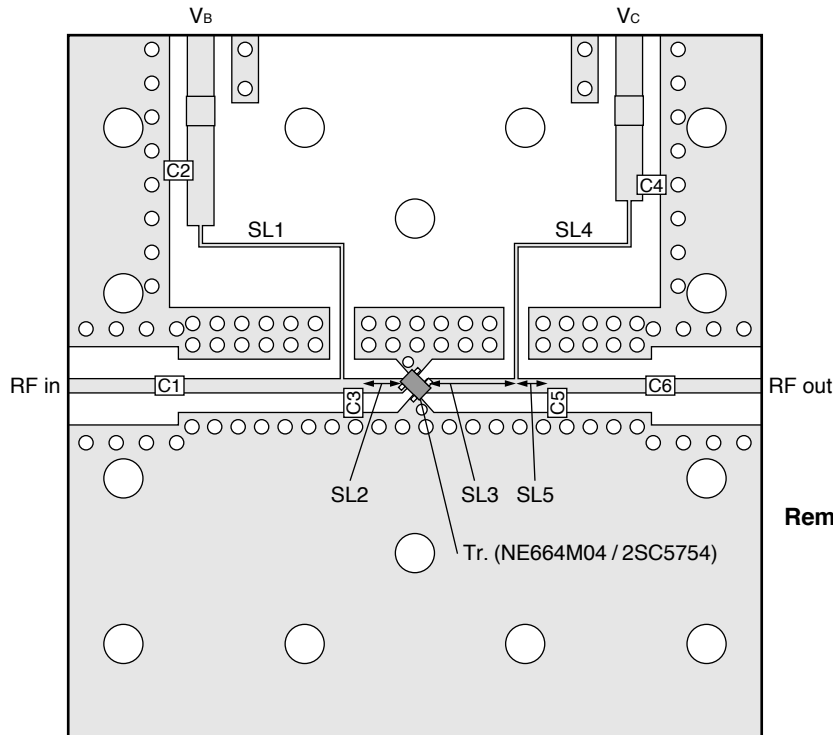


Cordless Phone
f = 0.9 GHz



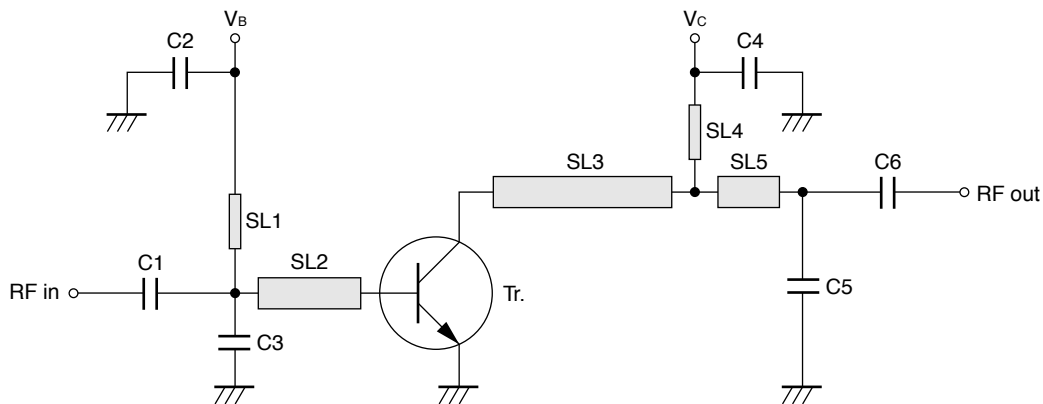
EVALUATION CIRCUIT EXAMPLE : 1.8 GHz PA EVALUATION BOARD

PCB Pattern and Element Layout



- Remarks**
1. 38 × 38 mm, t = 0.4 mm, $\epsilon_r = 4.55$ double-sided copper-clad polyimide board
 2. Back side : GND pattern
 3. Solder plating on pattern
 4. ○ ○ : Through holes

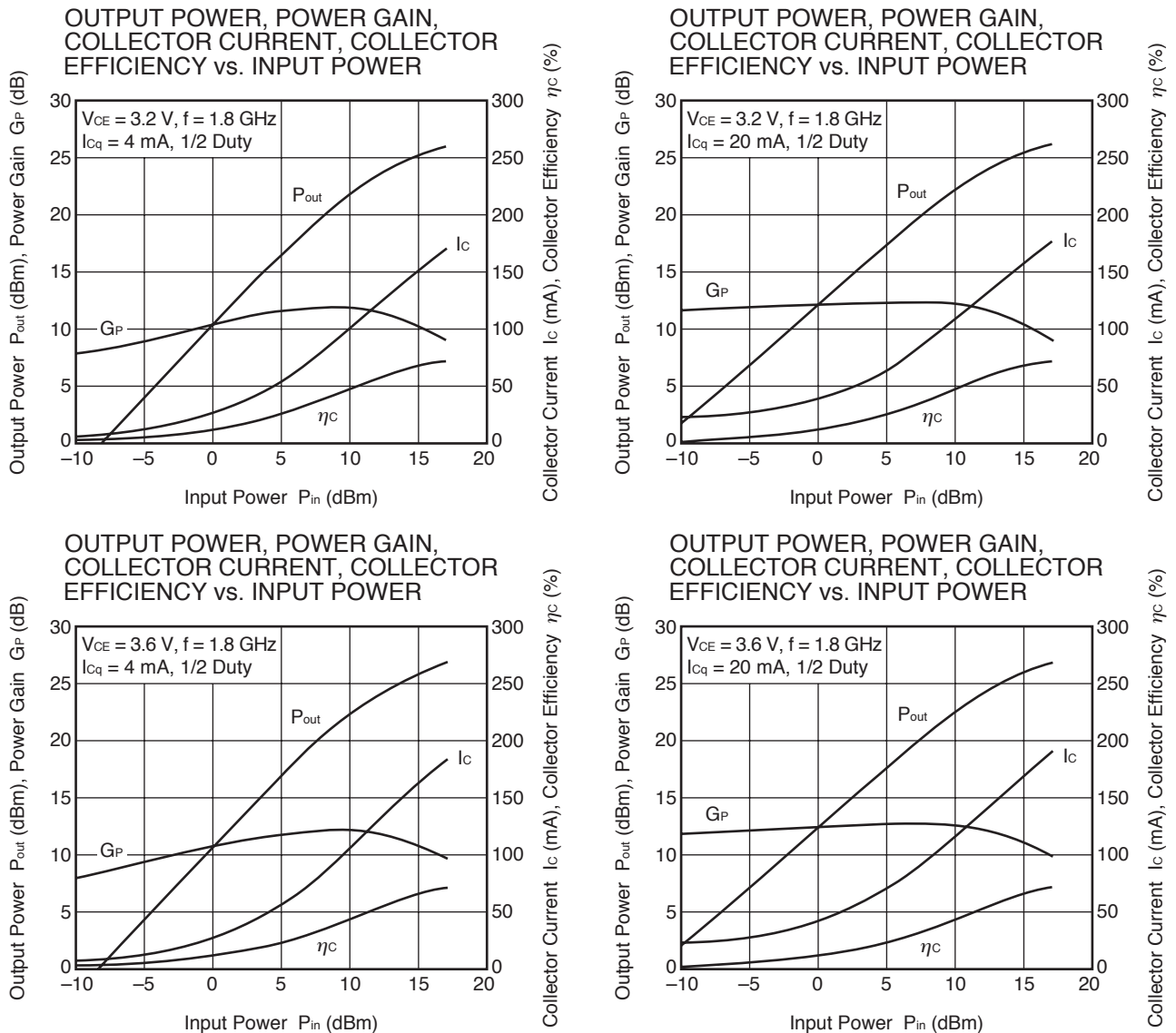
Equivalent Circuit



Parts List

Parts	Value	Size	Classification
C1, C6	18 pF		Multiplayer ceramic chip capacitor
C2	3 300 pF		Multiplayer ceramic chip capacitor
C3	3 pF		Multiplayer ceramic chip capacitor
C4	15 pF		Multiplayer ceramic chip capacitor
C5	1.5 pF		Multiplayer ceramic chip capacitor
SL1, SL4		w = 0.20 mm	Strip line
SL2		w = 0.76 mm, l = 2.5 mm	Strip line
SL3		w = 0.76 mm, l = 5 mm	Strip line
SL5		w = 0.76 mm, l = 1.5 mm	Strip line

EXAMPLE OF CHARACTERISTICS FOR 1.8 GHz PA EVALUATION BOARD



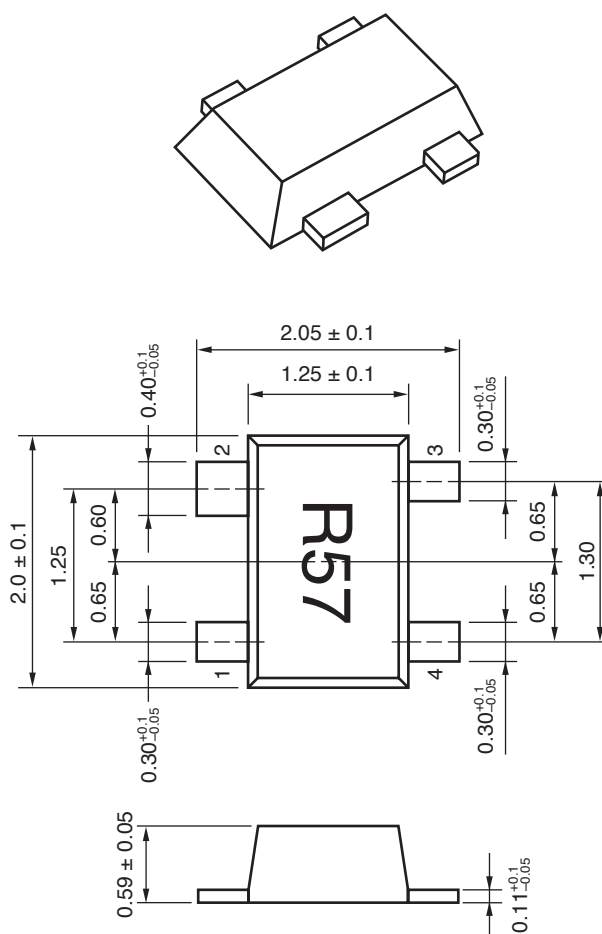
Remark The graphs indicate nominal characteristics.

S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)



PIN CONNECTIONS

1. Emitter
2. Collector
3. Emitter
4. Base

NOTICE

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. California Eastern Laboratories and Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
2. California Eastern Laboratories has used reasonable care in preparing the information included in this document, but California Eastern Laboratories does not warrant that such information is error free. California Eastern Laboratories and Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
3. California Eastern Laboratories and Renesas Electronics do not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of California Eastern Laboratories or Renesas Electronics or others.
4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. California Eastern Laboratories and Renesas Electronics assume no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc. "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc. Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. California Eastern Laboratories and Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by California Eastern Laboratories or Renesas Electronics.
6. You should use the Renesas Electronics products described in this document within the range specified by California Eastern Laboratories, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. California Eastern Laboratories shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or systems manufactured by you.
8. Please contact a California Eastern Laboratories sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. California Eastern Laboratories and Renesas Electronics assume no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations.
10. It is the responsibility of the buyer or distributor of California Eastern Laboratories, who distributes, disposes of, or otherwise places the Renesas Electronics product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, California Eastern Laboratories and Renesas Electronics assume no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics products.
11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of California Eastern Laboratories.
12. Please contact a California Eastern Laboratories sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

NOTE 1: "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

NOTE 2: "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

NOTE 3: Products and product information are subject to change without notice.

CEL Headquarters • 4590 Patrick Henry Drive, Santa Clara, CA 95054 • Phone (408) 919-2500 • www.cel.com

For a complete list of sales offices, representatives and distributors,
Please visit our website: www.cel.com/contactus

AMEYA360

Components Supply Platform

Authorized Distribution Brand :



Website :

Welcome to visit www.ameya360.com

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd
Minhang District, Shanghai , China

➤ Sales :

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

➤ Customer Service :

Email service@ameya360.com

➤ Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com